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AMENDMENTS TO THE CLAIMS

1. **(Previously presented)** A resin for a photoresist composition comprising a –CR¹R²OH group only at a terminal of a principal chain of the resin; (a1) a structural unit derived from a (meth)acrylate ester having an acid dissociable, dissolution inhibiting group; and (a2) a structural unit derived from a (meth)acrylate ester having a lactone ring, wherein R¹ and R² each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of R¹ and R² is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups.

- 2. (Canceled).
- 3. **(Original)** A resin for a photoresist composition according to claim 1, wherein said electron attractive group is a fluorine atom or a fluorinated alkyl group.
- 4. (Canceled)
- 5. (Canceled)
- 6. (Canceled)
- 7. (Canceled)
- 8. (Canceled)
- 9. **(Previously presented)** A resin for a photoresist composition according to claim 1, further comprising (a3) a structural unit derived from a (meth)acrylate ester having a hydroxyl group.
- 10. **(Previously presented)** A resin for a photoresist composition according to claim 1, with a weight average molecular weight of no more than 12,000.

Appl. No. : 10/557,694

Filed: November 22, 2005

11. **(Previously presented)** A photoresist composition, comprising a resin for a photoresist composition according to claim 1.

12. (Previously presented) A photoresist composition comprising:

a resin comprising a -CR¹R²OH group only at a terminal of a principal chain of the resin, wherein R¹ and R² each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of R¹ and R² is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups; and an acid generator as a component (B).

- 13. **(Original)** A photoresist composition according to claim 12, comprising as said component (B), (b-0) an onium salt that comprises a fluorinated alkylsulfonate ion as an anion.
- 14. **(Original)** A photoresist composition according to claim 12, comprising as said component (B), a sulfonium compound represented by either of general formulas (b-1) and (b-2) shown below:

$$R^{2}$$
 S^{+} N SO_{2} \cdots $(b-1)$ R^{3} SO_{2} \cdots $(b-1)$ R^{2} S^{+} N \cdots $(b-2)$ R^{3} $O_{2}S$ Z

wherein, X represents an alkylene group of 2 to 6 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; Y and Z each represent, independently, an alkyl group of 1 to 10 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; R^1 to R^3 each represent, independently, an aryl group or an alkyl group, and at least one of R^1 to R^3 is an aryl group.

Appl. No. : 10

10/557,694

Filed

November 22, 2005

15. **(Original)** A photoresist composition according to claim 14, further comprising as said component (B), (b-0) an onium salt that comprises a fluorinated alkylsulfonate ion as an anion.

16. (Currently amended) A photoresist composition according to claim 12, further comprising:

a resin comprising a CR⁴R²OH group only at a terminal of a principal chain of the resin, , wherein R⁴ and R² each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of R⁴ and R² is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups; and

a nitrogen-containing organic compound.

17. (Currently amended) A method for forming a resist pattern, comprising the steps of:

applying a photoresist composition that comprises a resin comprising a $-CR^1R^2OH$ group only at a terminal of a principal chain of the resin, [[,]] wherein R^1 and R^2 each represent, independently, an alkyl group, halogen atom, or halogenated alkyl group, and at least one of R^1 and R^2 is an electron attractive group selected from the group consisting of halogen atoms and halogenated alkyl groups to a surface of a substrate;

performing selective exposure through a desired mask pattern; and performing developing to form a resist pattern.

- 18. (Canceled)
- 19. (Canceled)
- 20. (Canceled)
- 21. (Canceled)
- 22. (Canceled)

Appl. No. : 10/557,694 Filed : November 22, 2005

- 23. (Canceled)
- (Canceled) 24.